2.5V Drive Nch MOS FET

RTQ020N03

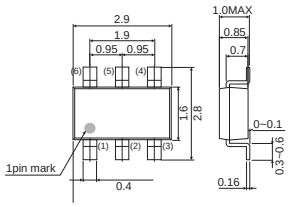
●Structure
Silicon N-channel MOS FET

●Features
1) Low On-resistance.
2) Space saving, small surface mount package (TSMT6).
3) Low voltage drive (2.5V drive).

●Applications
Switching

●External dimensions (Unit : mm)

TSMT6



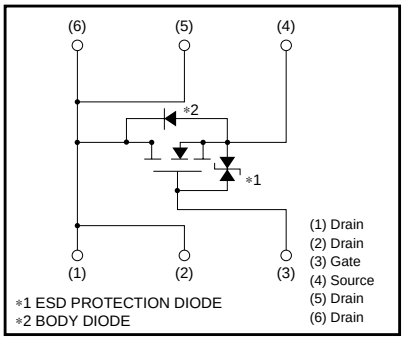
Each lead has same dimensions

Abbreviated symbol : QS

●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RTQ020N03		○

●Inner circuit



*1 ESD PROTECTION DIODE
*2 BODY DIODE

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	12	V
Drain current	Continuous	I_D	±2.0	A
	Pulsed	I_{DP} *1	±8.0	A
Source current (Body diode)	Continuous	I_S	1.0	A
	Pulsed	I_{SP} *1	8.0	A
Total power dissipation		P_D *2	1.25	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	100	°C/W

* Mounted on a ceramic board

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	10	μA	V_{GS}=12V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	30	–	–	V	I_D= 1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	V_{DS}= 30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	0.5	–	1.5	V	V_{DS}= 10V, I_D= 1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	89	125	mΩ	I_D= 2A, V_{GS}= 4.5V
		–	94	132	mΩ	I_D= 2A, V_{GS}= 4V
		–	138	194	mΩ	I_D= 2.A, V_{GS}= 2.5V
Forward transfer admittance	$\|Y_{fs}\|$ *	2.0	–	–	S	V_{DS}= 10V, I_D= 2A
Input capacitance	C_{iss}	–	135	–	pF	V_{DS}= 10V
Output capacitance	C_{oss}	–	35	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	25	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	8	–	ns	V_{DD}≒ 15V
Rise time	t_r *	–	11	–	ns	I_D= 1A
Turn-off delay time	$t_{d\ (off)}$ *	–	17	–	ns	V_{GS}= 4.5V R_L=15Ω
Fall time	t_f *	–	9	–	ns	R_G=10Ω
Total gate charge	Q_g *	–	2.4	3.3	nC	V_{DD}≒ 15V
Gate-source charge	Q_{gs} *	–	0.5	–	nC	V_{GS}= 4.5V
Gate-drain charge	Q_{gd} *	–	0.7	–	nC	I_D= 2A

*Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	–	–	1.2	V	I_S= 4A, V_{GS}=0V

*Pulsed

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